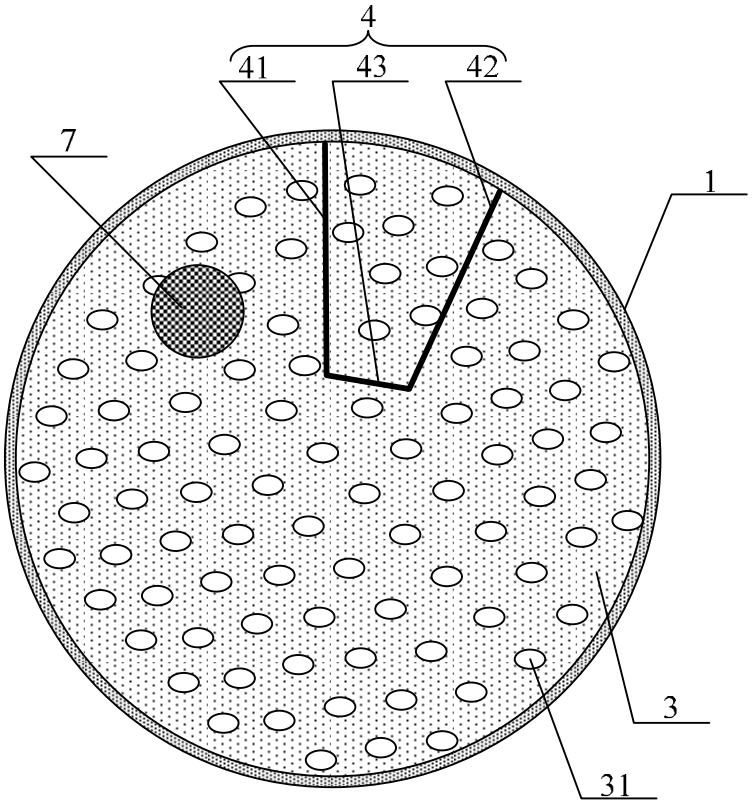

FIG. 1

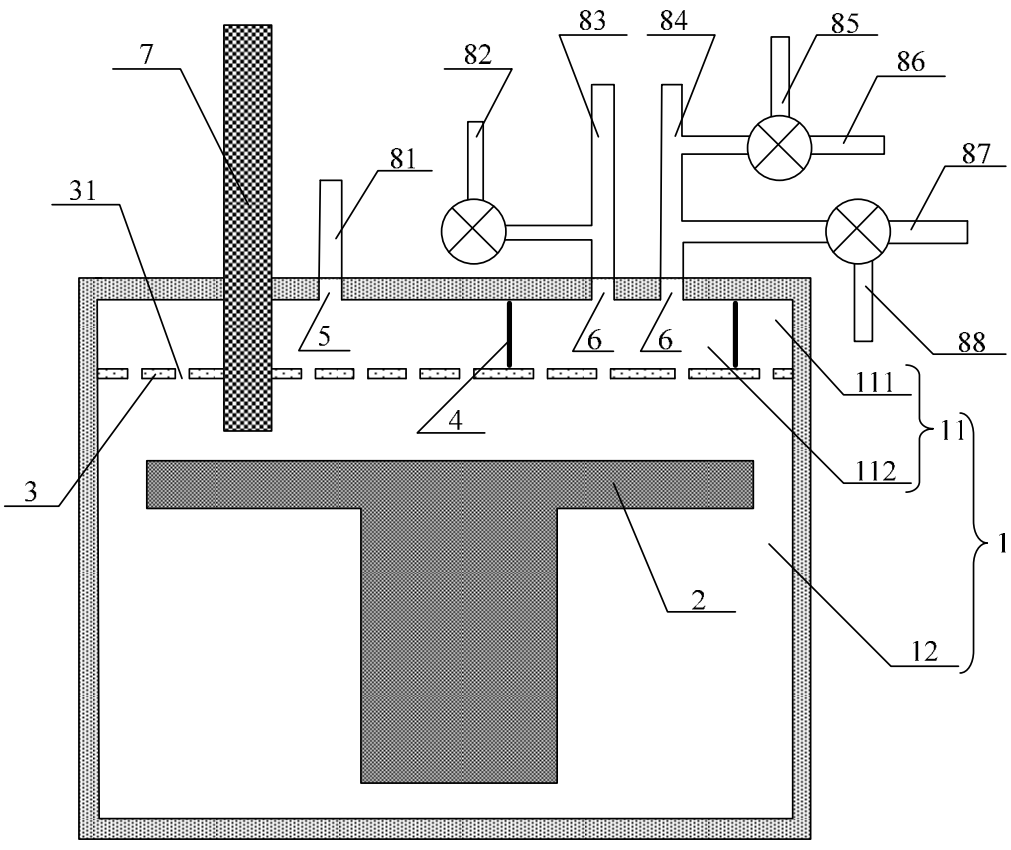

FIG. 2

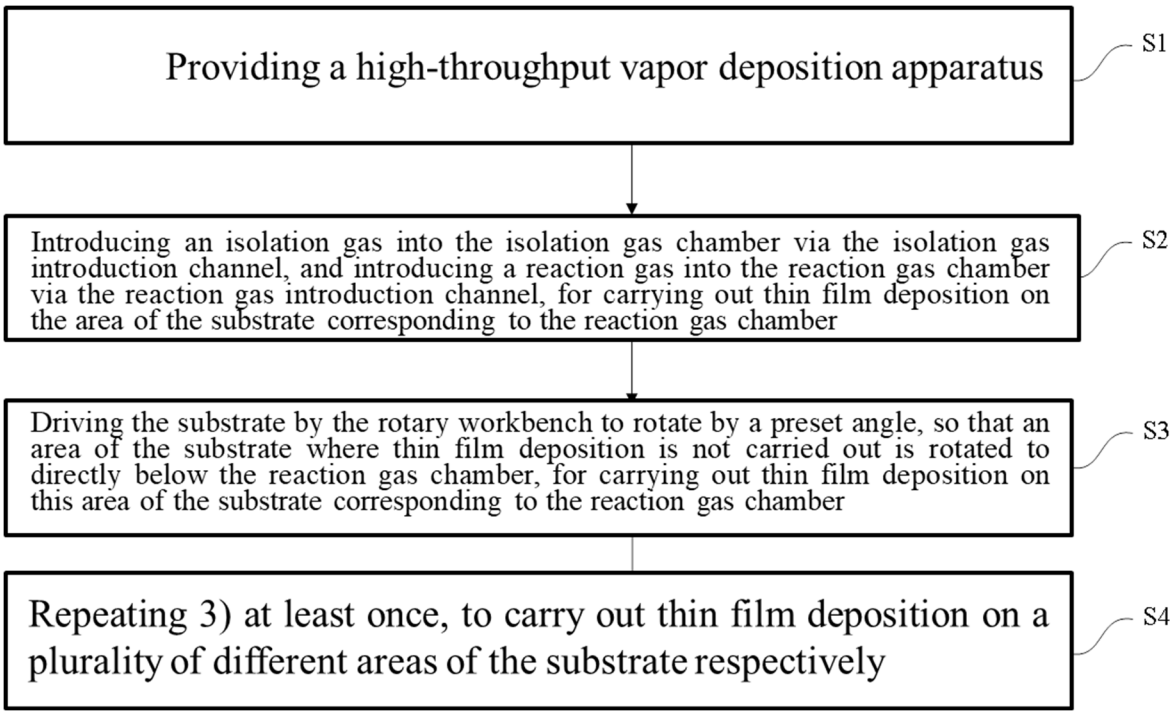
Providing a high-throughput vapor deposition apparatus
S1
Introducing an isolation gas into the isolation gas chamber via the isolation gas introduction channel, and introducing a reaction gas into the reaction gas chamber via the reaction gas introduction channel, for carrying out thin film deposition on the area of the substrate corresponding to the reaction gas chamber
S2
Driving the substrate by the rotary workbench to rotate by a preset angle, so that an area of the substrate where thin film deposition is not carried out is rotated to directly below the reaction gas chamber, for carrying out thin film deposition on this area of the substrate corresponding to the reaction gas chamber
S3
Repeating 3) at least once, to carry out thin film deposition on a plurality of different areas of the substrate respectively
S4

FIG. 3